NLHV4051, NLHV4052, NLHV4053

Analog Multiplexers/Demultiplexers

The NLHV4051, NLHV4052, and NLHV4053 analog multiplexers are digitally−controlled analog switches. The NLHV4051 effectively implements an SP8T solid state switch, the NLHV4052 a DP4T, and the NLHV4053 a Triple SPDT. All three devices feature low ON impedance and very low OFF leakage current. Control of analog signals up to the complete supply voltage range can be achieved.

Features

- Triple Diode Protection on Control Inputs
- Switch Function is Break Before Make
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Analog Voltage Range ($V_{DD} - V_{EE}$) = 3.0 to 18 V
  Note: V_{EE} must be ≤ V_{SS}
- Linearized Transfer Characteristics
- Low−noise − 12 nV/$\sqrt{\text{Cycle}}$, f ≥ 1.0 kHz Typical
- Pin−for−Pin Replacement for CD4051, CD4052, and CD4053
- For 4PDT Switch, See MC14551B
- For Lower R_{ON}, Use the HC4051, HC4052, or HC4053 High−Speed CMOS Devices
- These Devices are Pb−Free and are RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range (Referenced to V_{EE}, $V_{SS} \geq V_{EE}$)	−0.5 to +18.0	V
V_{in}, V_{out}	Input or Output Voltage Range (DC or Transient) (Referenced to V_{SS} for Control Inputs and V_{EE} for Switch I/O)	−0.5 to V_{DD} + 0.5	V
I_{in}	Input Current (DC or Transient) per Control Pin	+10	mA
I_{SW}	Switch Through Current	±25	mA
P_D	Power Dissipation per Package (Note 1)	500	mW
T_A	Ambient Temperature Range	−55 to +125	°C
T_{stg}	Storage Temperature Range	−65 to +150	°C
T_L	Lead Temperature (8−Second Soldering)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: “D/DW” Packages: −7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high−impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \leq (V_{in}$ or $V_{out}) \leq V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS}, V_{EE} or V_{DD}). Unused outputs must be left open.

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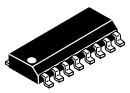
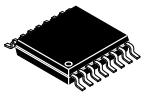
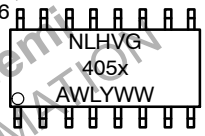


SOIC−16
D SUFFIX
CASE 751B



TSSOP−16
DT SUFFIX
CASE 948F

MARKING DIAGRAMS



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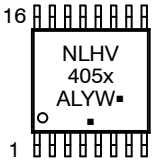


TSSOP−16

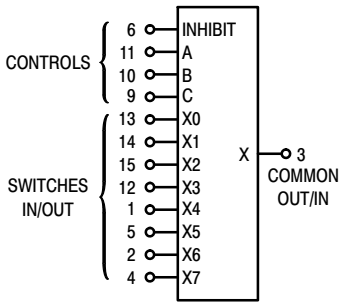
x	= 1, 2, or 3
A	= Assembly Location
WL, L	= Wafer Lot
Y	= Year
WW, W	= Work Week
G or ▪	= Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

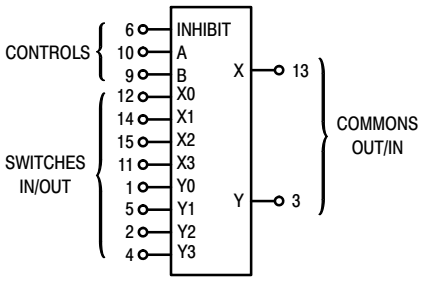
See detailed ordering and shipping information in the package dimensions section on page 9 of this data sheet.

NLHV4051
8−Channel Analog Multiplexer/Demultiplexer



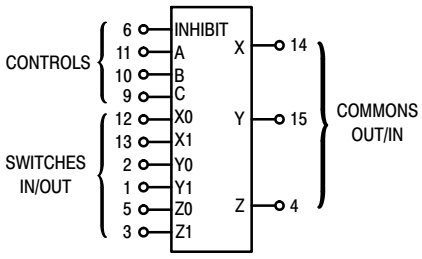
V_{DD} = PIN 16
V_{SS} = PIN 8
V_{EE} = PIN 7

NLHV4052
Dual 4−Channel Analog Multiplexer/Demultiplexer



V_{DD} = PIN 16
V_{SS} = PIN 8
V_{EE} = PIN 7

NLHV4053
Triple 2−Channel Analog Multiplexer/Demultiplexer

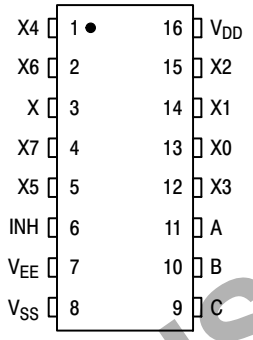


V_{DD} = PIN 16
V_{SS} = PIN 8
V_{EE} = PIN 7

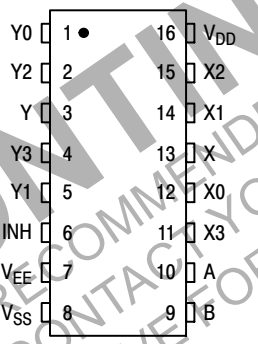
Note: Control Inputs referenced to V_{SS}, Analog Inputs and Outputs reference to V_{EE}. V_{EE} must be ≤ V_{SS}.

PIN ASSIGNMENT

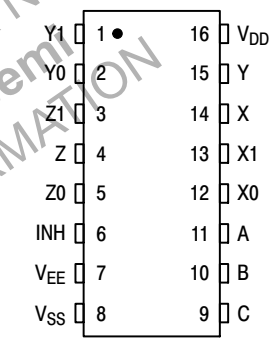
NLHV4051



NLHV4052



NLHV4053



ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	V_{DD}	Test Conditions	−55°C Min	−55°C Max	25°C Min	25°C Typ (Note 2)	25°C Max	125°C Min	125°C Max	Unit
SUPPLY REQUIREMENTS (Voltages Referenced to V_{EE})											
Power Supply Voltage Range	V_{DD}	–	$V_{DD} - 3.0 \geq V_{SS} \geq V_{EE}$	3.0	18	3.0	–	18	3.0	18	V
Quiescent Current Per Package	I_{DD}	5.0 10 15	Control Inputs: $V_{in} = V_{SS}$ or V_{DD}, Switch I/O: $V_{EE} \leq V_{I/O} \leq V_{DD}$, and $\Delta V_{switch} \leq$ 500 mV (Note 3)	– – –	5.0 10 20	– – –	0.005 0.010 0.015	5.0 10 20	– – –	150 300 600	μA
Total Supply Current (Dynamic Plus Quiescent, Per Package	$I_{D(AV)}$	5.0 10 15	$T_A = 25°C$ only (The channel component, $(V_{in} - V_{out})/R_{on}$, is not included.)	Typical			(0.07 μA/kHz) f + I_{DD} (0.20 μA/kHz) f + I_{DD} (0.36 μA/kHz) f + I_{DD}				μA
CONTROL INPUTS — INHIBIT, A, B, C (Voltages Referenced to V_{SS})											
Low−Level Input Voltage	V_{IL}	5.0 10 15	R_{on} = per spec, I_{off} = per spec	– – –	1.5 3.0 4.0	– – –	2.25 4.50 6.75	1.5 3.0 4.0	– – –	1.5 3.0 4.0	V
High−Level Input Voltage	V_{IH}	5.0 10 15	R_{on} = per spec, I_{off} = per spec	3.5 7.0 11	– – –	3.5 7.0 11	2.75 5.50 8.25	– – –	3.5 7.0 11	– – –	V
Input Leakage Current	I_{in}	15	V_{in} = 0 or V_{DD}	–	±0.1	–	±0.00001	±0.1	–	1.0	μA
Input Capacitance	C_{in}	–		–	–	–	5.0	7.5	–	–	pF
SWITCHES IN/OUT AND COMMONS OUT/IN — X, Y, Z (Voltages Referenced to V_{EE})											
Recommended Peak−to−Peak Voltage Into or Out of the Switch	$V_{I/O}$	–	Channel On or Off	0	V_{DD}	0	–	V_{DD}	0	V_{DD}	V_{PP}
Recommended Static or Dynamic Voltage Across the Switch (Note 3) (Figure 5)	ΔV_{switch}	–	Channel On	0	600	0	–	600	0	300	mV
Output Offset Voltage	V_{OO}	–	V_{in} = 0 V, No Load	–	–	–	10	–	–	–	μV
ON Resistance	R_{on}	5.0 10 15	$\Delta V_{switch} \leq$ 500 mV (Note 3) $V_{in} = V_{IL}$ or V_{IH} (Control), and V_{in} = 0 to V_{DD} (Switch)	– – –	800 400 220	– – –	250 120 80	1050 500 280	– – –	1200 520 300	Ω
ΔON Resistance Between Any Two Channels in the Same Package	ΔR_{on}	5.0 10 15		– – –	70 50 45	– – –	25 10 10	70 50 45	– – –	135 95 65	Ω
Off−Channel Leakage Current (Figure 10)	I_{off}	15	$V_{in} = V_{IL}$ or V_{IH} (Control) Channel to Channel or Any One Channel	–	±100	–	±0.05	±100	–	±1000	nA
Capacitance, Switch I/O	$C_{I/O}$	–	Inhibit = V_{DD}	–	–	–	10	–	–	–	pF
Capacitance, Common O/I	$C_{O/I}$	–	Inhibit = V_{DD} (NLHV4051) (NLHV4052) (NLHV4053)	 – – –	 – – –	 – – –	 60 32 17	 – – –	 – – –	 – – –	pF
Capacitance, Feedthrough (Channel Off)	$C_{I/O}$	– –	Pins Not Adjacent Pins Adjacent	– –	– –	– –	0.15 0.47	– –	– –	– –	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Data labeled “Typ” is not to be used for design purposes, but is intended as an indication of the IC’s potential performance.
3. For voltage drops across the switch (ΔV_{switch}) > 600 mV (> 300 mV at high temperature), excessive V_{DD} current may be drawn, i.e. the current out of the switch may contain both V_{DD} and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded. (See first page of this data sheet.)

ELECTRICAL CHARACTERISTICS (Note 4) (C_L = 50 pF, T_A = 25°C) ($V_{EE} \le V_{SS}$ unless otherwise indicated)

Characteristic	Symbol	$V_{DD} - V_{EE}$ Vdc	Typ (Note 5) All Types	Max	Unit
Propagation Delay Times (Figure 6)	t_{PLH}, t_{PHL}				ns
Switch Input to Switch Output (R_L = 1 kΩ)					
NLHV4051					
t_{PLH}, t_{PHL} = (0.17 ns/pF) C_L + 26.5 ns		5.0	35	90	
t_{PLH}, t_{PHL} = (0.08 ns/pF) C_L + 11 ns		10	15	40	
t_{PLH}, t_{PHL} = (0.06 ns/pF) C_L + 9.0 ns		15	12	30	
NLHV4052					ns
t_{PLH}, t_{PHL} = (0.17 ns/pF) C_L + 21.5 ns		5.0	30	75	
t_{PLH}, t_{PHL} = (0.08 ns/pF) C_L + 8.0 ns		10	12	30	
t_{PLH}, t_{PHL} = (0.06 ns/pF) C_L + 7.0 ns		15	10	25	
NLHV4053					ns
t_{PLH}, t_{PHL} = (0.17 ns/pF) C_L + 16.5 ns		5.0	25	65	
t_{PLH}, t_{PHL} = (0.08 ns/pF) C_L + 4.0 ns		10	8.0	20	
t_{PLH}, t_{PHL} = (0.06 ns/pF) C_L + 3.0 ns		15	6.0	15	
Inhibit to Output (R_L = 10 kΩ, $V_{EE} = V_{SS}$) Output "1" or "0" to High Impedance, or High Impedance to "1" or "0" Level	t_{PHZ}, t_{PLZ}, t_{PZH}, t_{PZL}				ns
NLHV4051		5.0	350	700	
		10	170	340	
		15	140	280	
NLHV4052		5.0	300	600	ns
		10	155	310	
		15	125	250	
NLHV4053		5.0	275	550	ns
		10	140	280	
		15	110	220	
Control Input to Output (R_L = 1 kΩ, $V_{EE} = V_{SS}$)	t_{PLH}, t_{PHL}				ns
NLHV4051		5.0	360	720	
		10	160	320	
		15	120	240	
NLHV4052		5.0	325	650	ns
		10	130	260	
		15	90	180	
NLHV4053		5.0	300	600	ns
		10	120	240	
		15	80	160	
Second Harmonic Distortion (R_L = 10KΩ, f = 1 kHz) V_{in} = 5 V_{PP}	–	10	0.07	–	%
Bandwidth (Figure 7) (R_L = 50 Ω, V_{in} = 1/2 (V_{DD}–V_{EE}) p–p, C_L = 50pF 20 Log (V_{out}/V_{in}) = – 3 dB)	BW	10	17	–	MHz
Off Channel Feedthrough Attenuation (Figure 7) R_L = 1KΩ, V_{in} = 1/2 (V_{DD} – V_{EE}) p–p f_{in} = 4.5 MHz — NLHV4051 f_{in} = 30 MHz — NLHV4052 f_{in} = 55 MHz — NLHV4053	–	10	–50	–	dB
Channel Separation (Figure 8) (R_L = 1 kΩ, V_{in} = 1/2 (V_{DD}–V_{EE}) p–p, f_{in} = 3.0 MHz	–	10	–50	–	dB
Crosstalk, Control Input to Common O/I (Figure 9) (R_1 = 1 kΩ, R_L = 10 kΩ Control $t_{TLH} = t_{THL}$ = 20 ns, Inhibit = V_{SS})	–	10	75	–	mV

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. The formulas given are for the typical characteristics only at 25°C.
5. Data labelled "Typ" is not lo be used for design purposes but In intended as an indication of the IC's potential performance.

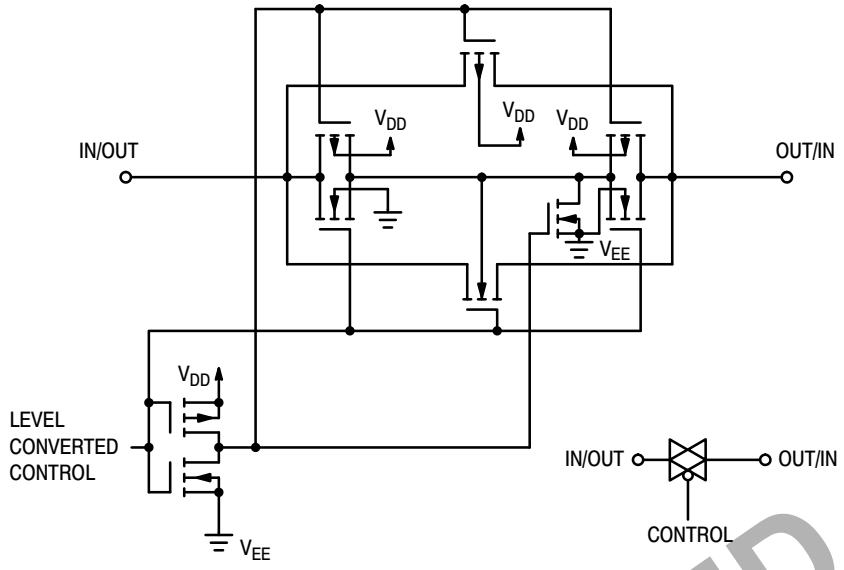


Figure 1. Switch Circuit Schematic

TRUTH TABLE

Control Inputs				ON Switches					
	Select								
Inhibit	C*	B	A	NLHV4051	NLHV4052		NLHV4053		
0	0	0	0	X0	Y0	X0	Z0	Y0	X0
0	0	0	1	X1	Y1	X1	Z0	Y0	X1
0	0	1	0	X2	Y2	X2	Z0	Y1	X0
0	0	1	1	X3	Y3	X3	Z0	Y1	X1
0	1	0	0	X4			Z1	Y0	X0
0	1	0	1	X5			Z1	Y0	X1
0	1	1	0	X6			Z1	Y1	X0
0	1	1	1	X7			Z1	Y1	X1
1	x	x	x	None	None		None		

*Not applicable for MC14052
x = Don't Care

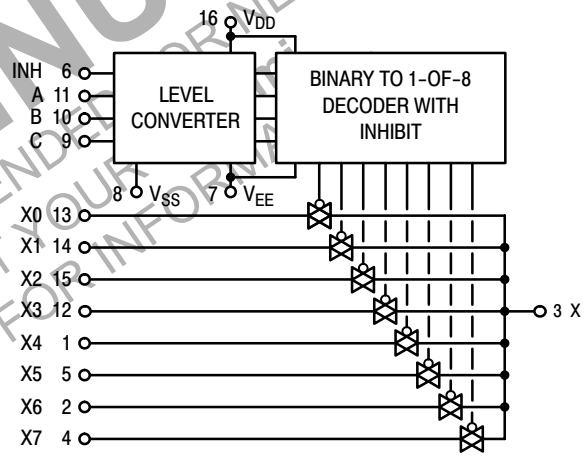


Figure 2. NLHV4051 Functional Diagram

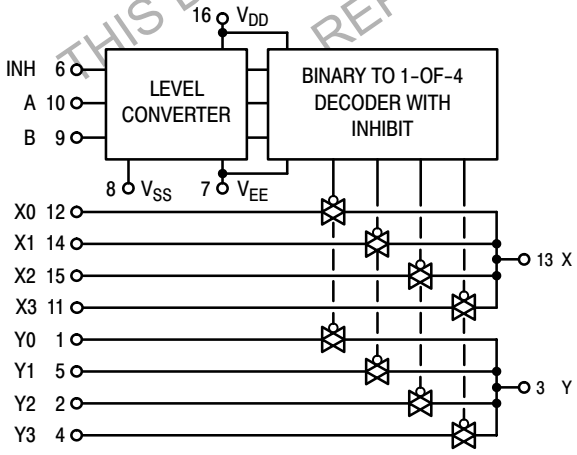


Figure 3. NLHV4052 Functional Diagram

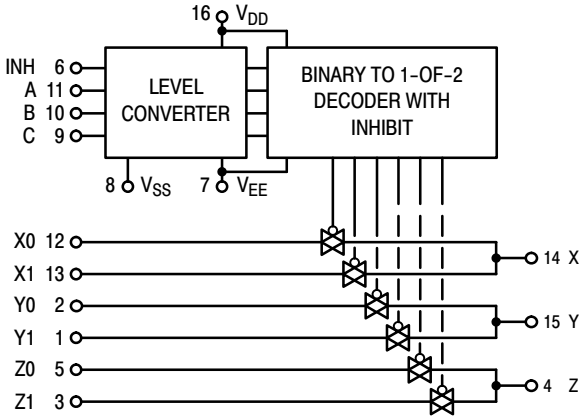


Figure 4. NLHV4053 Functional Diagram

TEST CIRCUITS

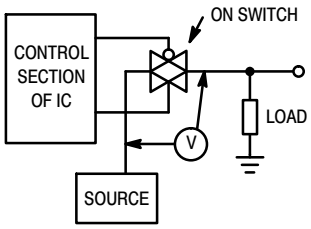


Figure 5. ΔV Across Switch

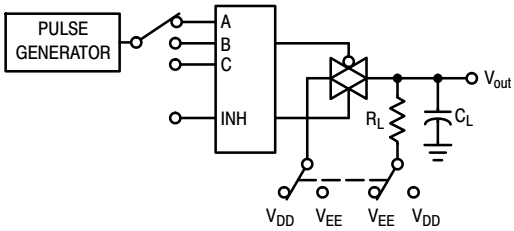


Figure 6. Propagation Delay Times, Control and Inhibit to Output

A, B, and C inputs used to turn ON or OFF the switch under test.

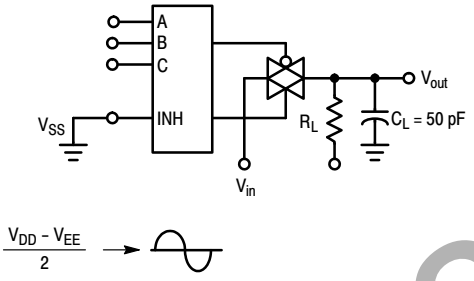


Figure 7. Bandwidth and Off−Channel Feedthrough Attenuation

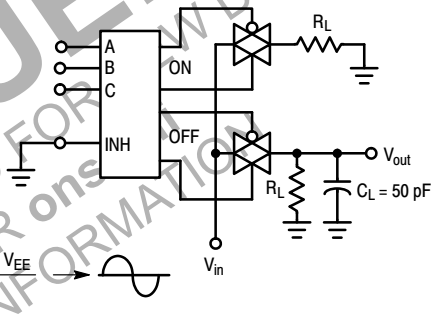


Figure 8. Channel Separation (Adjacent Channels Used For Setup)

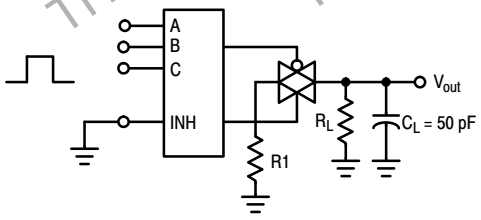


Figure 9. Crosstalk, Control Input to Common O/I

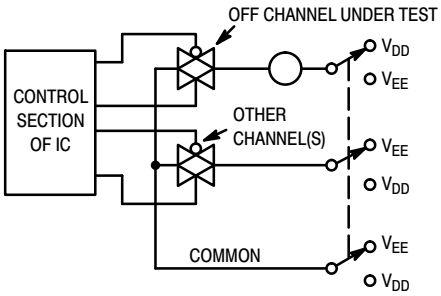


Figure 10. Off Channel Leakage

NOTE: See also Figures 7 and 8 in the MC14016B data sheet.

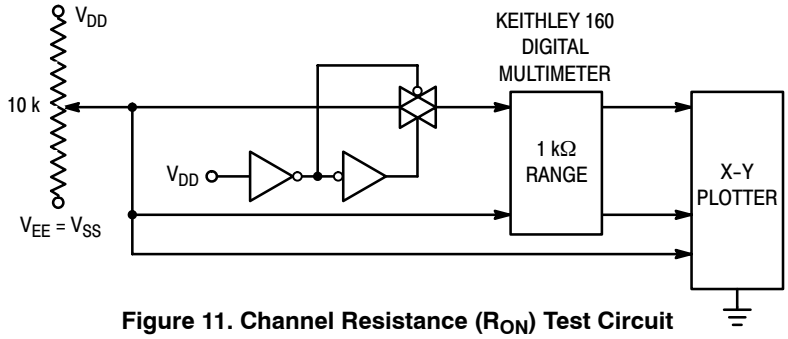


Figure 11. Channel Resistance (R_{ON}) Test Circuit

TYPICAL RESISTANCE CHARACTERISTICS

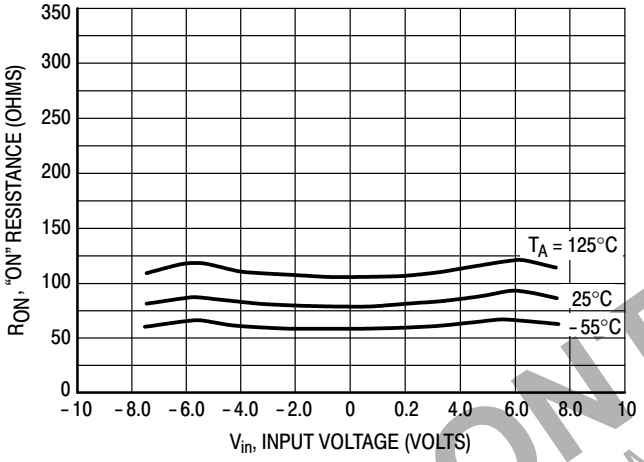


Figure 12. V_{DD} = 7.5 V, V_{EE} = − 7.5 V

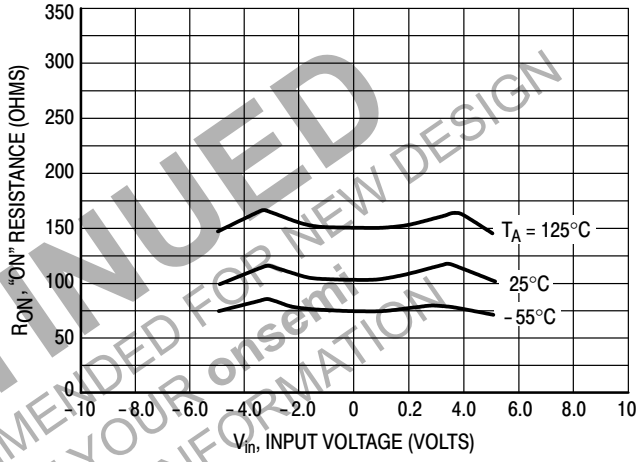


Figure 13. V_{DD} = 5.0 V, V_{EE} = − 5.0 V

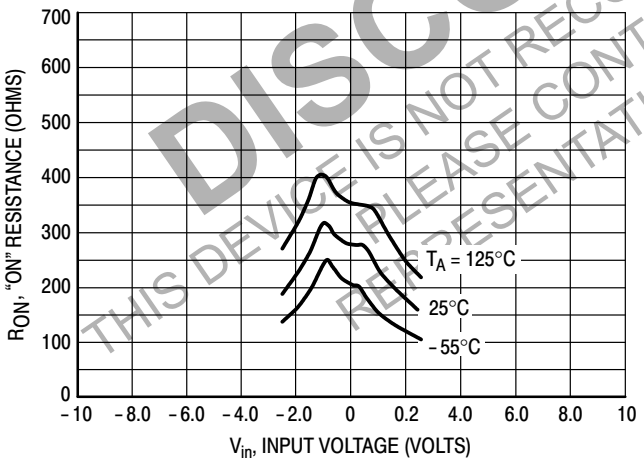


Figure 14. V_{DD} = 2.5 V, V_{EE} = − 2.5 V

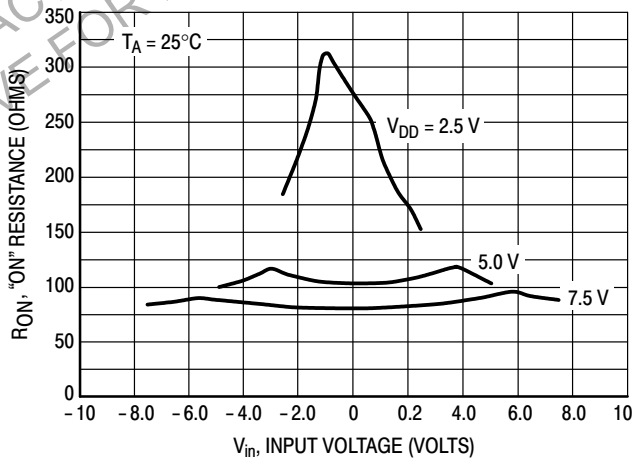


Figure 15. Comparison at 25°C, $V_{DD} = -V_{EE}$

APPLICATIONS INFORMATION

Figure A illustrates use of the on−chip level converter detailed in Figures 2, 3, and 4. The 0−to−5 V Digital Control signal is used to directly control a 9 V_{p-p} analog signal.

The digital control logic levels are determined by V_{DD} and V_{SS}. The V_{DD} voltage is the logic high voltage; the V_{SS} voltage is logic low. For the example, V_{DD} = +5 V = logic high at the control inputs; V_{SS} = GND = 0 V = logic low.

The maximum analog signal level is determined by V_{DD} and V_{EE}. The V_{DD} voltage determines the maximum recommended peak above V_{SS}. The V_{EE} voltage determines the maximum swing below V_{SS}. For the example, V_{DD} − V_{SS} = 5 V maximum swing above V_{SS}; V_{SS} − V_{EE} = 5 V maximum swing below V_{SS}. The example shows a ±4.5 V signal which allows a 1/2 volt margin at each peak. If voltage transients above V_{DD} and/or below V_{EE} are anticipated on the analog channels, external diodes (Dx) are recommended as shown in Figure B. These diodes should be small signal types able to absorb the maximum anticipated current surges during clipping.

The *absolute* maximum potential difference between V_{DD} and V_{EE} is 18.0 V. Most parameters are specified up to 15 V which is the *recommended* maximum difference between V_{DD} and V_{EE}.

Balanced supplies are not required. However, V_{SS} must be greater than or equal to V_{EE}. For example, V_{DD} = +10 V, V_{SS} = +5 V, and V_{EE} − 3 V is acceptable. See the Table below.

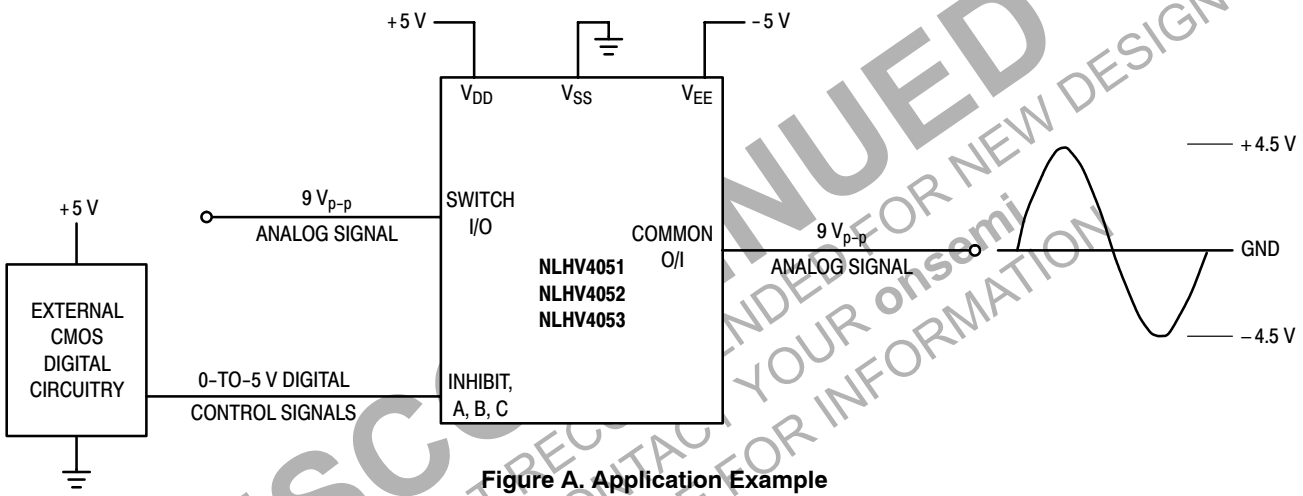


Figure A. Application Example

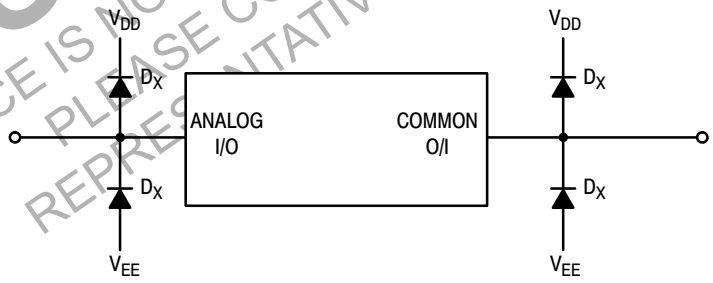


Figure B. External Germanium or Schottky Clipping Diodes

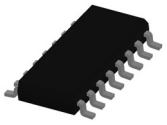
POSSIBLE SUPPLY CONNECTIONS

V_{DD} In Volts	V_{SS} In Volts	V_{EE} In Volts	Control Inputs Logic High/Logic Low In Volts	Maximum Analog Signal Range In Volts
+8	0	−8	+8/0	+8 to −8 = 16 V_{p-p}
+5	0	−12	+5/0	+5 to −12 = 17 V_{p-p}
+5	0	0	+5/0	+5 to 0 = 5 V_{p-p}
+5	0	−5	+5/0	+5 to −5 = 10 V_{p-p}
+10	+5	−5	+10/ +5	+10 to −5 = 15 V_{p-p}

ORDERING INFORMATION

Device	Package	Shipping†
NLHV4051DR2G	SOIC−16 (Pb−Free)	2500 / Tape & Reel
NLHV4051DTR2G	TSSOP−16 (Pb−Free)	2500 / Tape & Reel
NLHV4052DR2G	SOIC−16 (Pb−Free)	2500 / Tape & Reel
NLHV4052DTR2G	TSSOP−16 (Pb−Free)	2500 / Tape & Reel
NLHV4053DR2G (In Development)	SOIC−16 (Pb−Free)	2500 / Tape & Reel
NLHV4053DTR2G (In Development)	TSSOP−16 (Pb−Free)	2500 / Tape & Reel

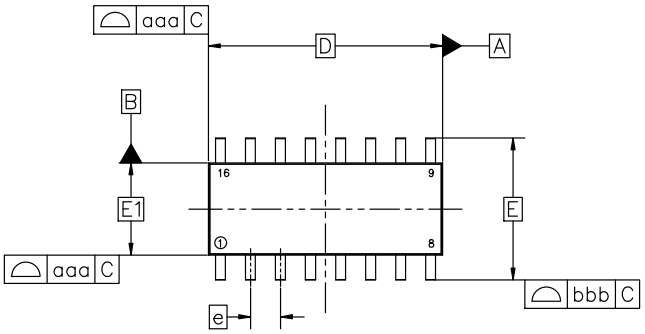
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



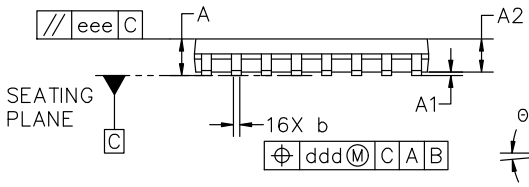
SOIC−16 9.90x3.90x1.37 1.27P
CASE 751B
ISSUE M

DATE 18 OCT 2024

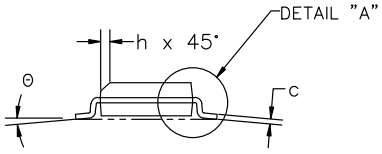
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
5. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE b DIMENSION AT MAXIMUM MATERIAL CONDITION.



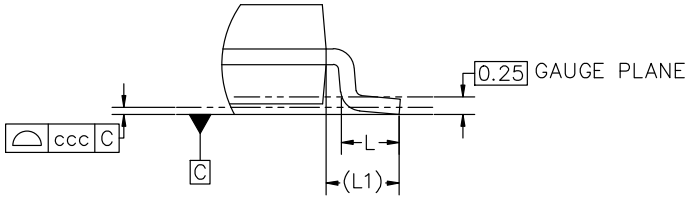
TOP VIEW



SIDE VIEW

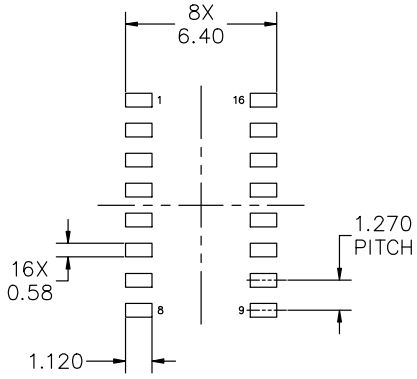


END VIEW



DETAIL "A"
Scale 3:1

MILLIMETERS			
DIM	MIN	NOM	MAX
A	1.35	1.55	1.75
A1	0.10	0.18	0.25
A2	1.25	1.37	1.50
b	0.35	0.42	0.49
c	0.19	0.22	0.25
D	9.90 BSC		
E	6.00 BSC		
E1	3.90 BSC		
e	1.27 BSC		
h	0.25	−−−	0.50
L	0.40	0.83	1.25
L1	1.05 REF		
Θ	0°	−−−	7°
TOLERANCE OF FORM AND POSITION			
aaa	0.10		
bbb	0.20		
ccc	0.10		
ddd	0.25		
eee	0.10		



RECOMMENDED MOUNTING FOOTPRINT

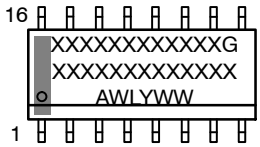
*FOR ADDITIONAL INFORMATION ON OUR PB−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE onsemi SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D

DOCUMENT NUMBER:	**98ASB42566B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	**SOIC−16 9.90X3.90X1.37 1.27P**		**PAGE 1 OF 2**

SOIC−16 9.90x3.90x1.37 1.27P
CASE 751B
ISSUE M

DATE 18 OCT 2024

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:

PIN	
1.	COLLECTOR
2.	BASE
3.	EMITTER
4.	NO CONNECTION
5.	EMITTER
6.	BASE
7.	COLLECTOR
8.	COLLECTOR
9.	BASE
10.	EMITTER
11.	NO CONNECTION
12.	EMITTER
13.	BASE
14.	COLLECTOR
15.	EMITTER
16.	COLLECTOR

STYLE 2:

PIN	
1.	CATHODE
2.	ANODE
3.	NO CONNECTION
4.	CATHODE
5.	CATHODE
6.	NO CONNECTION
7.	ANODE
8.	CATHODE
9.	CATHODE
10.	ANODE
11.	NO CONNECTION
12.	CATHODE
13.	CATHODE
14.	NO CONNECTION
15.	ANODE
16.	CATHODE

STYLE 3:

PIN	
1.	COLLECTOR, DYE #1
2.	BASE, #1
3.	EMITTER, #1
4.	COLLECTOR, #1
5.	COLLECTOR, #2
6.	BASE, #2
7.	EMITTER, #2
8.	COLLECTOR, #2
9.	COLLECTOR, #3
10.	BASE, #3
11.	EMITTER, #3
12.	COLLECTOR, #3
13.	COLLECTOR, #4
14.	BASE, #4
15.	EMITTER, #4
16.	COLLECTOR, #4

STYLE 4:

PIN	
1.	COLLECTOR, DYE #1
2.	COLLECTOR, #1
3.	COLLECTOR, #2
4.	COLLECTOR, #2
5.	COLLECTOR, #3
6.	COLLECTOR, #3
7.	COLLECTOR, #4
8.	COLLECTOR, #4
9.	BASE, #4
10.	EMITTER, #4
11.	BASE, #3
12.	EMITTER, #3
13.	BASE, #2
14.	EMITTER, #2
15.	BASE, #1
16.	EMITTER, #1

STYLE 5:

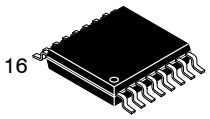
PIN	
1.	DRAIN, DYE #1
2.	DRAIN, #1
3.	DRAIN, #2
4.	DRAIN, #2
5.	DRAIN, #3
6.	DRAIN, #3
7.	DRAIN, #4
8.	DRAIN, #4
9.	GATE, #4
10.	SOURCE, #4
11.	GATE, #3
12.	SOURCE, #3
13.	GATE, #2
14.	SOURCE, #2
15.	GATE, #1
16.	SOURCE, #1

STYLE 6:

PIN	
1.	CATHODE
2.	CATHODE
3.	CATHODE
4.	CATHODE
5.	CATHODE
6.	CATHODE
7.	CATHODE
8.	CATHODE
9.	ANODE
10.	ANODE
11.	ANODE
12.	ANODE
13.	ANODE
14.	ANODE
15.	ANODE
16.	ANODE

STYLE 7:

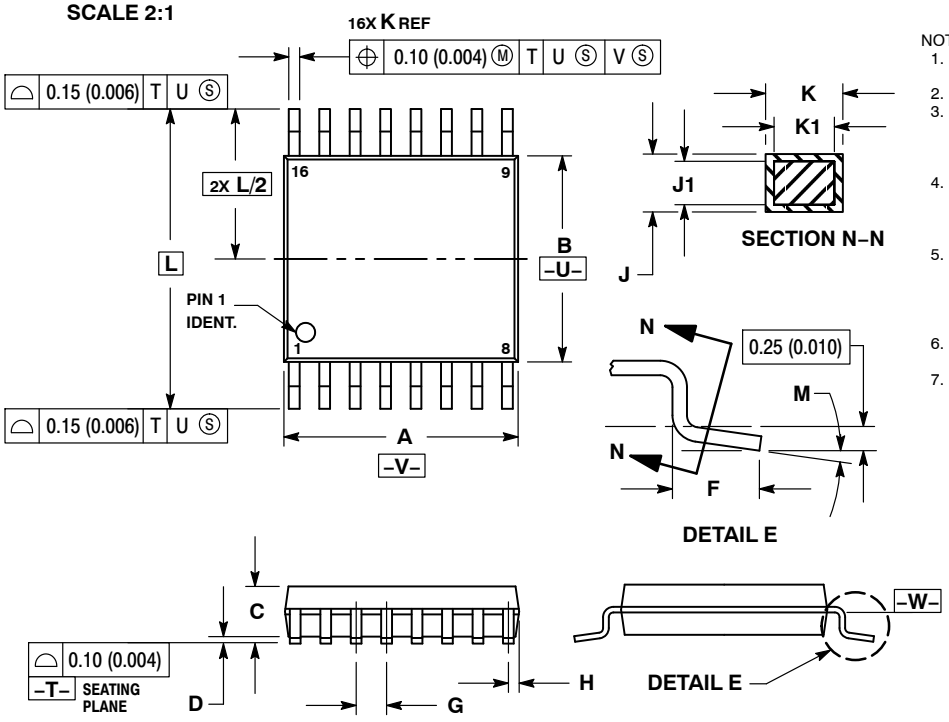
PIN	
1.	SOURCE N-CH
2.	COMMON DRAIN (OUTPUT)
3.	COMMON DRAIN (OUTPUT)
4.	GATE P-CH
5.	COMMON DRAIN (OUTPUT)
6.	COMMON DRAIN (OUTPUT)
7.	COMMON DRAIN (OUTPUT)
8.	SOURCE P-CH
9.	SOURCE P-CH
10.	COMMON DRAIN (OUTPUT)
11.	COMMON DRAIN (OUTPUT)
12.	COMMON DRAIN (OUTPUT)
13.	GATE N-CH
14.	COMMON DRAIN (OUTPUT)
15.	COMMON DRAIN (OUTPUT)
16.	SOURCE N-CH



SCALE 2:1

TSSOP−16 WB
CASE 948F
ISSUE B

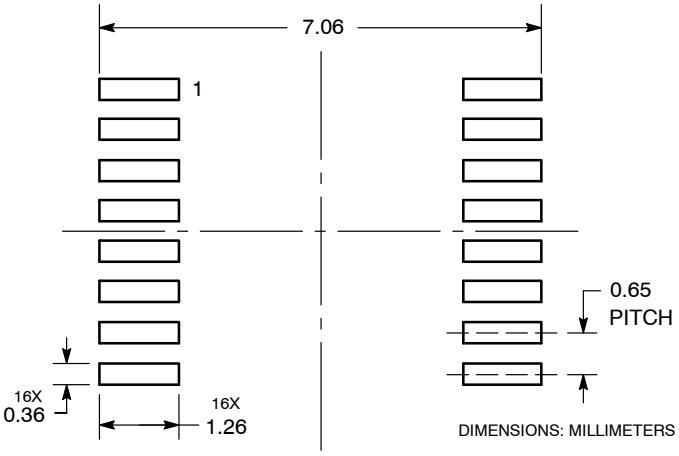
DATE 19 OCT 2006



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

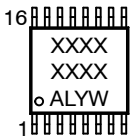
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	−−−	1.20	−−−	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXX	= Specific Device Code
A	= Assembly Location
L	= Wafer Lot
Y	= Year
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G or ▪	= Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	**TSSOP−16**		**PAGE 1 OF 1**

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